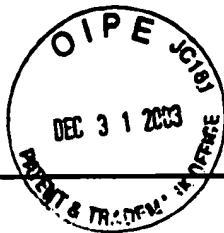


FORM PTO - 1449				ATTORNEY DOCKET NO.: ASC-043C2			
INFORMATION DISCLOSURE STATEMENT				APPLICANT(S): Fitzgerald <i>et al.</i>			
				SERIAL NO.: 10/625,018			
				FILING DATE: July 23, 2003 GROUP: ²⁸²² Not yet assigned			
U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
KBD	A1	4,010,045	03/01/1977	Ruehrwein			
	A2	4,710,788	12/01/1987	Dämbkes <i>et al.</i>			
	A3	4,990,979	02/05/1991	Otto			
	A4	4,997,776	03/05/1991	Haramé <i>et al.</i>			
	A5	5,013,681	05/07/1991	Godbey <i>et al.</i>			
	A6	5,155,571	10/13/1992	Wang <i>et al.</i>			
	A7	5,166,084	11/24/1992	Pfiester			
	A8	5,177,583	01/05/1993	Endo <i>et al.</i>			
	A9	5,202,284	04/13/1993	Kamins <i>et al.</i>			
	A10	5,207,864	05/04/1993	Bhat <i>et al.</i>			
	A11	5,208,182	05/04/1993	Narayan <i>et al.</i>			
	A12	5,212,110	05/18/1993	Pfiester <i>et al.</i>			
	A13	5,221,413	06/22/1993	Brasen <i>et al.</i>			
	A14	5,241,197	08/31/1993	Murakami <i>et al.</i>			
	A15	5,250,445	10/05/1993	Bean <i>et al.</i>			
	A16	5,285,086	02/08/1994	Fitzgerald			
	A17	5,291,439	03/01/1994	Kauffmann <i>et al.</i>			
	A18	5,298,452	03/29/1994	Meyerson			
	A19	5,310,451	05/10/1994	Tejwani <i>et al.</i>			
	A20	5,316,958	05/31/1994	Meyerson			
	A21	5,346,848	09/13/1994	Gruppen-Shemansky <i>et al.</i>			
	A22	5,374,564	12/20/1994	Bruel			
Y	A23	5,399,522	03/21/1995	Ohori			
EXAMINER				DATE CONSIDERED 6/18/2004			



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KBD	A24	5,413,679	05/09/1995	Godbey			
	A25	5,426,069	06/20/1995	Selvakumar <i>et al.</i>			
	A26	5,426,316	06/20/1995	Mohammad			
	A27	5,442,205	08/15/1995	Brasen <i>et al.</i>			
	A28	5,461,243	10/24/1995	Ek <i>et al.</i>			
	A29	5,461,250	10/24/1995	Burghartz <i>et al.</i>			
	A30	5,462,883	10/31/1995	Dennard <i>et al.</i>			
	A31	5,476,813	12/19/1995	Naruse			
	A32	5,479,033	12/26/1995	Baca <i>et al.</i>			
	A33	5,484,664	01/16/1996	Kitahara <i>et al.</i>			
	A34	5,523,243	06/04/1996	Mohammad			
	A35	5,523,592	06/04/1996	Nakagawa <i>et al.</i>			
	A36	5,534,713	07/09/1996	Ismail <i>et al.</i>			
	A37	5,536,361	07/16/1996	Kondo <i>et al.</i>			
	A38	5,540,785	07/30/1996	Dennard <i>et al.</i>			
	A39	5,596,527	01/21/1997	Tomioka <i>et al.</i>			
	A40	5,617,351	04/01/1997	Bertin <i>et al.</i>			
	A41	5,630,905	05/20/1997	Lynch <i>et al.</i>			
	A42	5,659,187	08/19/1997	Legoues <i>et al.</i>			
	A43	5,683,934	11/04/1997	Candelaria			
	A44	5,698,869	12/16/1997	Yoshimi <i>et al.</i>			
	A45	5,714,777	02/03/1998	Ismail <i>et al.</i>			
	A46	5,728,623	03/17/1998	Mori			
	A47	5,739,567	04/14/1998	Wong			
EXAMINER <i>John E. Perry</i>				DATE CONSIDERED <i>6/18/2004</i>			



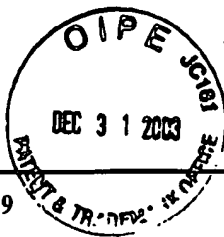
FORM PTO - 1449 INFORMATION DISCLOSURE STATEMENT				ATTORNEY DOCKET NO.: ASC-043C2 APPLICANT(S): Fitzgerald et al. SERIAL NO.: 10/625,018 FILING DATE: July 23, 2003 GROUP: Not yet assigned			
U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
KED	A48	5,759,898	06/02/1998	Ek et al.			
	A49	5,786,612	07/28/1998	Otani et al.			
	A50	5,792,679	08/11/1998	Nakato			
	A51	5,808,344	09/15/1998	Ismail et al.			
	A52	5,847,419	12/08/1998	Imai et al.			
	A53	5,877,070	03/02/1999	Goesele et al.			
	A54	5,891,769	04/06/1999	Liaw et al.			
	A55	5,906,708	05/25/1999	Robinson et al.			
	A56	5,912,479	06/15/1999	Mori et al.			
	A57	5,943,560	08/24/1999	Chang et al.			
	A58	5,963,817	10/05/1999	Chu et al.			
	A59	5,966,622	10/12/1999	Levine et al.			
	A60	5,998,807	12/07/1999	Lustig et al.			
	A61	6,033,974	03/07/2000	Henley et al.			
	A62	6,033,995	03/07/2000	Muller.			
	A63	6,058,044	05/02/2000	Sugiura et al.			
	A64	6,074,919	06/13/2000	Gardner et al.			
	A65	6,096,590	08/01/2000	Chan et al.			
	A66	6,103,559	08/15/2000	Gardner et al.			
	A67	6,107,653	08/22/2000	Fitzgerald			
	A68	6,117,750	09/12/2000	Bensahel et al.			
	A69	6,130,453	10/10/2000	Mei et al.			
	A70	6,133,799	10/17/2000	Favors et al.			
V	A71	6,140,687	10/31/2000	Shimomura et al.			
EXAMINER <i>John B. [Signature]</i>				DATE CONSIDERED 6/18/2004			



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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
KPD	A72	6,143,636	11/07/2000	Forbes <i>et al.</i>			
	A73	6,153,495	11/28/2000	Kub <i>et al.</i>			
	A74	6,154,475	11/28/2000	Soref <i>et al.</i>			
	A75	6,160,303	12/12/2000	Fattaruso			
	A76	6,162,688	12/19/2000	Gardner <i>et al.</i>			
	A77	6,184,111	02/06/2001	Henley <i>et al.</i>			
	A78	6,191,007	02/20/2001	Matsui <i>et al.</i>			
	A79	6,191,432	02/20/2001	Sugiyama <i>et al.</i>			
	A80	6,194,722	02/27/2001	Fiorini <i>et al.</i>			
	A81	6,207,977	03/27/2001	Augusto			
	A82	6,210,988	04/03/2001	Howe <i>et al.</i>			
	A83	6,218,677	04/17/2001	Broekaert			
	A84	6,232,138	05/15/2001	Fitzgerald <i>et al.</i>			
	A85	6,235,567	05/22/2001	Huang			
	A86	6,242,324	06/05/2001	Kub <i>et al.</i>			
	A87	6,251,755	06/26/2001	Furukawa <i>et al.</i>			
	A88	6,261,929	07/17/2001	Gehrke <i>et al.</i>			
	A89	6,271,551	08/07/2001	Schmitz <i>et al.</i>			
	A90	6,271,726	08/07/2001	Fransis <i>et al.</i>			
	A91	6,291,321	09/18/2001	Fitzgerald			
	A92	6,313,016	11/06/2001	Kibbel <i>et al.</i>			
	A93	6,316,301	11/13/2001	Kant			
↓	A94	6,323,108	11/27/2001	Kub <i>et al.</i>			
EXAMINER <i>John R. Perry</i>				DATE CONSIDERED 6/18/2004			



FORM PTO - 1449 INFORMATION DISCLOSURE STATEMENT				ATTORNEY DOCKET NO.: ASC-043C2 APPLICANT(S): Fitzgerald <i>et al.</i> SERIAL NO.: 10/625,018 FILING DATE: July 23, 2003 GROUP: Not yet assigned					
U.S. PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
KBD	A95	6,329,063	12/11/2001	Lo <i>et al.</i>					
	A96	6,335,546	01/01/2002	Tsuda <i>et al.</i>					
	A97	6,339,232	01/15/2002	Takagi					
	A98	6,350,993	02/26/2002	Chu <i>et al.</i>					
	A99	6,368,733	04/09/2002	Nishinaga					
	A100	6,372,356	04/16/2002	Thornton <i>et al.</i>					
	A101	6,399,970	06/04/2002	Kubo <i>et al.</i>					
	A102	6,403,975	06/11/2002	Brunner <i>et al.</i>					
	A103	6,407,406	06/18/2002	Tezuka					
	A104	6,425,951	07/30/2002	Chu <i>et al.</i>					
	A105	6,429,061	08/06/2002	Rim					
	A106	6,521,041	02/18/2003	Wu <i>et al.</i>					
	A107	6,555,839	04/29/2003	Fitzgerald					
	A108	6,602,613	08/05/2003	Fitzgerald					01/17/2001
	A109	2001/0003364	06/14/2001	Sugawara <i>et al.</i>					
	A110	2002/0100942	08/01/2001	Fitzgerald <i>et al.</i>					
	A111	2002/0123197	09/05/2002	Fitzgerald <i>et al.</i>					
	A112	2002/0125471	09/12/2002	Fitzgerald <i>et al.</i>					
Y	A113	2002/0140031	10/03/2002	Rim					
FOREIGN PATENT DOCUMENTS									
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KBD	B1	41 01 167	07/23/1992	DE				N	Abstract
	B2	0 514 018	11/19/1992	EP				N	Y
Y	B3	0 587 520	03/16/1994	EP				N	Y
EXAMINER <i>John B. Jones</i>					DATE CONSIDERED 6/18/2004				



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	B5	0 828 296	03/11/1998	EP				N	Y	
	B6	0 829 908	03/18/1998	EP				N	Y	
	B7	0 838 858	04/29/1998	EP				N	Abstract	
	B8	1 020 900	07/19/2000	EP				N	Y	
	B9	1 174 928	01/23/2002	EP				N	Y	
	B10	2 342 777	04/19/2000	GB				Y	Y	
	B11	5-166724	07/02/1993	JP				N	Abstract	
	B12	6-177046	06/24/1994	JP				N	Abstract	
	B13	6-252046	09/09/1994	JP				Y	Y	
	B14	7-94420	04/07/1995	JP				N	N	
	B15	7-240372	09/12/1995	JP				N	Abstract	
	B16	10-270685	10/09/1998	JP				N	Y	
	B17	2000-021783	01/21/2000	JP				N	Y	
	B18	2000-031491	01/28/2000	JP				N	Y	
	B19	2001-319935	11/16/2001	JP				N	Y	
	B20	2002-076334	03/15/2002	JP				N	Y	
	B21	2002-164520	06/07/2002	JP				N	Y	
	B22	2002-289533	10/04/2002	JP				N	Y	
	B23	98/59365	12/30/1998	WO				N	Y	
	B24	99/53539	10/21/1999	WO				N	Y	
	B25	00/48239	08/17/2000	WO				N	Y	
	B26	00/54338	09/14/2000	WO				N	Y	
	B27	01/022482	03/29/2001	WO				N	Y	
	B28	01/54202	07/26/2001	WO				N	Y	
	B29	01/93338	12/06/2001	WO				N	Y	
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FOREIGN PATENT DOCUMENTS

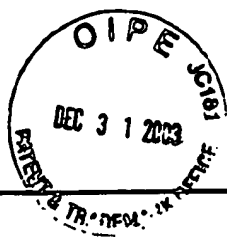
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		B31 02/13262	02/14/2002	WO				N	Y
		B32 02/15244	02/21/2002	WO				N	Y
		B33 02/27783	04/04/2002	WO				N	Y
		B34 02/47168	06/13/2002	WO				N	Y
		B35 02/071488	09/12/2002	WO				N	Y
		B36 02/071491	09/12/2002	WO				N	Y
		B37 02/071495	09/12/2002	WO				N	Y
↓		B38 02/082514	10/17/2002	WO				N	Y

OTHER ART, JOURNAL ARTICLES, ETC.

EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
KBD	C1	Armstrong <i>et al.</i> , "Design of Si/SiGe Heterojunction Complementary Metal-Oxide-Semiconductor Transistors," <u>IEDM Technical Digest (1995 International Electron Devices Meeting)</u> , pp. 761-764.
	C2	Armstrong, "Technology for SiGe Heterostructure-Based CMOS Devices," PhD Thesis, Massachusetts Institute of Technology, 1999, pp. 1-154.
	C3	Augusto <i>et al.</i> , "Proposal for a New Process Flow for the Fabrication of Silicon-Based Complementary MOD-MOSFETs without Ion Implantation," <u>Thin Solid Films</u> , Vol. 294, No. 1-2 (February 15, 1997), pp. 254-258.
	C4	Barradas <i>et al.</i> , "RBS analysis of MBE-grown SiGe/(001) Si heterostructures with thin, high Ge content SiGe channels for HMOS transistors," <u>Modern Physics Letters B</u> , Vol. 15 (2001), abstract.
	C5	Borenstein <i>et al.</i> , "A New Ultra-Hard Etch-Stop Layer for High Precision Micromachining," Proceedings of the 1999 12th IEEE International Conference on Micro Electro Mechanical Systems (MEMS) (January 17-21, 1999), pp. 205-210.
↓	C6	Bouillon <i>et al.</i> , "Search for the optimal channel architecture for 0.18/0.12 μ m bulk CMOS experimental study," <u>IEEE</u> (1996), pp. 21.2.1-21.2.4.
EXAMINER		DATE CONSIDERED 6/18/2004



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OTHER ART, JOURNAL ARTICLES, ETC.		
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
KBD	C7	Bruel <i>et al.</i> , "@SMART CUT: A Promising New SOI Material Technology," Proceedings of the 1995 IEEE International SOI Conference (October 1995), pp. 178-179.
	C8	Bruel, "Silicon on Insulator Material Technology," <u>Electronic Letters</u> , Vol. 13, No. 14 (July 6, 1995), pp. 1201-1202.
	C9	Bufler <i>et al.</i> , "Hole transport in strained Si1-xGex alloys on Si1-yGeY substrates," <u>Journal of Applied Physics</u> , Vol. 84, No. 10 (November 15, 1998), pp. 5597-5602.
	C10	Burghartz <i>et al.</i> , "Microwave Inductors and Capacitors in Standard Multilevel Interconnect Silicon Technology," <u>IEEE Transactions on Microwave Theory and Techniques</u> , Vol. 44, No. 1 (January 1996), pp. 100-104.
	C11	Canaperi <i>et al.</i> , "Preparation of a relaxed Si-Ge layer on an insulator in fabricating high-speed semiconductor devices with strained epitaxial films," International Business Machines Corporation, USA (2002), abstract.
	C12	Carlin <i>et al.</i> , "High Efficiency GaAs-on-Si Solar Cells with High Voc using Graded Gesi Buffers," <u>IEEE - 2000</u> (2000), pp. 1006-1011.
	C13	Chang <i>et al.</i> , "Selective Etching of SiGe/Si Heterostructures," <u>Journal of the Electrochemical Society</u> , No. 1 (January 1991), pp. 202-204.
	C14	Cheng <i>et al.</i> , "Electron Mobility Enhancement in Strained-Si n-MOSFETs Fabricated on SiGe-on-Insulator (SGOI) Substrates," <u>IEEE Electron Device Letters</u> , Vol. 22, No. 7 (July 2001), pp. 321-323.
	C15	Cheng <i>et al.</i> , "Relaxed Silicon-Germanium on Insulator Substrate by Layer Transfer," <u>Journal of Electronic Materials</u> , Vol. 30, No. 12 (2001), pp. L37-L39.
	C16	Cullis <i>et al.</i> , "Growth ripples upon strained SiGe epitaxial layers on Si and misfit dislocation interactions," <u>Journal of Vacuum Science and Technology A</u> , Vol. 12, No. 4 (July/August 1994), pp. 1924-1931.
	C17	Currie <i>et al.</i> , "Carrier mobilities and process stability of strained Si n- and p-MOSFETs on SiGe virtual substrates," <u>Journal of Vacuum Science and Technology B</u> , Vol. 19, No. 6 (Nov/Dec 2001), pp. 2268-2279.
	C18	Currie <i>et al.</i> , "Controlling Threading Dislocation Densities in Ge on Si Using Graded SiGe Layers and Chemical-Mechanical Polishing," <u>Applied Physics Letters</u> , Vol. 72, Issue 14 (04/06/98), pp. 1718-1720.
	C19	Eaglesham <i>et al.</i> , "Dislocation-Free Stranski-Krastanow Growth of Ge on Si(100)," <u>Physical Review Letters</u> , Vol. 64, No. 16 (April 16, 1990), pp. 1943-1946.
	C20	Feijoo <i>et al.</i> , "Epitaxial Si-Ge Etch Stop Layers with Ethylene Diamine Pyrocatechol for Bonded and Etchback Silicon-on-Insulator," <u>Journal of Electronic Materials</u> , Vol. 23, No. 6 (June 1994), pp. 493-496.
	C21	Fischetti <i>et al.</i> , "Band structure, deformation potentials, and carrier mobility in strained Si, Ge, and SiGe alloys," <u>Journal of Applied Physics</u> , Vol. 80, No. 4 (August 15, 1996), pp. 2234-2252.
↓	C22	Fischetti, "Long-range Coulomb interactions in small Si devices. Part II. Effective electronmobility in thin-oxide structures," <u>Journal of Applied Physics</u> , Vol. 89, No. 2 (January 15, 2001), pp. 1232-1250.
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EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)		
WBD	C23	Fitzgerald <i>et al.</i> , "Dislocation dynamics in relaxed graded composition semiconductors," <u>Materials Science and Engineering</u> , B67 (1999), pp. 53-61.	
	C24	Fitzgerald <i>et al.</i> , "Relaxed GexSi1-x structures for III-V integration with Si and high mobility two-dimensional electron gases in Si," <u>Journal of Vacuum Science Technology</u> , B 10(4) (Jul/August 1992), pp. 1807-1819.	
	C25	Fitzgerald <i>et al.</i> , "Totally Relaxed GexSi1-x Layers with Low Threading Dislocation Densities Grown on Si Substrates," <u>Applied Physics Letters</u> , Vol. 59, No. 7 (August 12, 1991), pp. 811-813.	
	C26	Garone <i>et al.</i> , "Silicon vapor phase epitaxial growth catalysis by the presence of germane," <u>Applied Physics Letters</u> , Vol. 56, No. 13 (March 26, 1990), pp. 1275-1277.	
	C27	Gray <i>et al.</i> , "Analysis and Design of Analog Integrated Circuits," John Wiley & Sons, 1984, pp. 605-632.	
	C28	Grützmacher <i>et al.</i> , "Ge segregation in SiGe/Si heterostructures and its dependence on deposition technique and growth atmosphere," <u>Applied Physics Letters</u> , Vol. 63, No. 18 (November 1, 1993), pp. 2531-2533.	
	C29	Hackbarth <i>et al.</i> , "Alternatives to thick MBE-grown relaxed SiGe buffers," <u>Thin Solid Films</u> , Vol. 369, No. 1-2 (July 2000), pp. 148-151.	
	C30	Hackbarth <i>et al.</i> , "Strain relieved SiGe buffers for Si-based heterostructure field-effect transistors," <u>Journal of Crystal Growth</u> , Vol. 201/202 (1999), pp. 734-738.	
	C31	Herzog <i>et al.</i> , "SiGe-based FETs: buffer issues and device results," <u>Thin Solid Films</u> , Vol. 380 (2000), pp. 36-41.	
	C32	Höck <i>et al.</i> , "Carrier mobilities in modulation doped Si1-xGex heterostructures with respect to FET applications," <u>Thin Solid Films</u> , Vol. 336 (1998), pp. 141-144.	
	C33	Höck <i>et al.</i> , "High hole mobility in Si0.17 Ge0.83 channel metal-oxide-semiconductor field-effect transistors grown by plasma-enhanced chemical vapor deposition," <u>Applied Physics Letters</u> , Vol. 76, No. 26 (June 26, 2000), pp. 3920-3922.	
	C34	Höck <i>et al.</i> , "High performance 0.25 μ m p-type Ge/SiGe MODFETs," <u>Electronics Letters</u> , Vol. 34, No. 19 (September 17, 1998), pp. 1888-1889.	
	C35	Huang <i>et al.</i> , "High-quality strain-relaxed SiGe alloy grown on implanted silicon-on-insulator substrate," <u>Applied Physics Letters</u> , Vol. 76, No. 19 (May 8, 2000), pp. 2680-2682.	
	C36	Huang <i>et al.</i> , "The Impact of Scaling Down to Deep Submicron on CMOS RF Circuits," <u>IEEE Journal of Solid-State Circuits</u> , Vol. 33, No. 7 (July 1998), pp. 1023-1036.	
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✓	C38	Ishikawa <i>et al.</i> , "SiGe-on-insulator substrate using SiGe alloy grown Si(001)," <u>Applied Physics Letters</u> , Vol. 75, No. 7 (August 16, 1999), pp. 983-985.	
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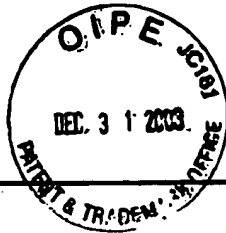
FORM PTO - 1449		ATTORNEY DOCKET NO.: ASC-043C2
INFORMATION DISCLOSURE STATEMENT		APPLICANT(S): Fitzgerald <i>et al.</i>
		SERIAL NO.: 10/625,018
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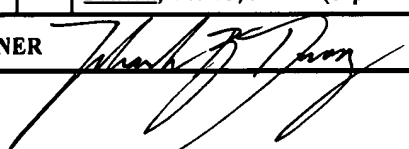


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ATTORNEY DOCKET NO.: ASC-043C2

SUPPLEMENTAL INFORMATION
DISCLOSURE STATEMENTAPPLICANT(S): Fitzgerald *et al.*

SERIAL NO.: 10/625,018

FILING DATE: July 23, 2003 GROUP: ~~2812~~ ²⁸²²

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KBD	B39	4-307974	10/30/1992	JP				N	Y (Abstract only)
↓	B40	7-106446	04/21/1995	JP				N	Y (Abstract only)
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OTHER ART, JOURNAL ARTICLES, ETC.


EXAM. INIT. OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)

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FORM PTO - 1449 SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT								ATTORNEY DOCKET NO.: ASC-043C2 APPLICANT(S): Fitzgerald <i>et al.</i> SERIAL NO.: 10/625,018 FILING DATE: July 23, 2003 GROUP: 2822 2812			
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KBD	A122	2002/0043660	4/18/2002	Yamazaki <i>et al.</i>			6/25/2001				
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EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)		
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OTHER ART, JOURNAL ARTICLES, ETC.											
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